

#### **Features**

- Low V<sub>CE(sat)</sub>
- Fast Switching
- High Ruggedness
- Short-Circuit Rated



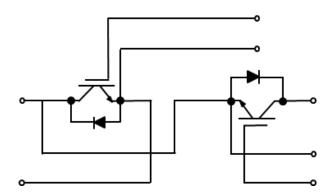
<b>Product Summary</b>				
V <sub>CES</sub>	1200V			
lc	200A			
V <sub>CE(sat),typ</sub>	1.6V			

## **Applications**

- General Purpose Inverters
- Frequency Converters
- Industrial Motor Drives
- Servos



#### **Internal Connection**



# IGBT, Inverter

#### **Absolute Maximum Ratings**

Parameter	Symbol	Limit	Unit	
Collector-to-Emitter Voltage	V <sub>CES</sub>	1200		
Gate-to-Emitter Voltage	±20		V	
Transient Gate-emitter Voltage ( $t_p \le 10 \mu s$ , D < 0.010)	V <sub>GES</sub>	±30		
Continuous DC Collector Current (T <sub>C</sub> = 100°C, T <sub>J</sub> = 175°C)	I <sub>CDC</sub>	200	^	
Repetitive Peak Collector Current (t <sub>p</sub> = 1ms)	I <sub>CRM</sub>	400	A	



## Electrical Characteristics (1), (2)

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Collector-to-Emitter Breakdown Voltage	BV <sub>CES</sub>	V <sub>GE</sub> = 0V, I <sub>C</sub> = 250μA	1200	-	-	V
Collector-to-Emitter Leakage Current	I <sub>CES</sub>	V <sub>CE</sub> = 1200V, V <sub>GE</sub> = 0V	-	-	5	mA
Gate-to-Emitter Leakage Current	I <sub>GES</sub>	V <sub>CE</sub> = 0V, V <sub>GE</sub> = ±20V	-	-	400	nA
Gate Threshold Voltage	$V_{\text{GE(th)}}$	$V_{CE} = V_{GE}$ , $I_C = 1.5$ mA	5.5	6.5	7.5	
		V <sub>GE</sub> = 15V, I <sub>C</sub> = 200A	-	1.6	1.95	V
Collector-to-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	V <sub>GE</sub> = 15V, I <sub>C</sub> = 200A, T <sub>J</sub> = 150°C	-	2.0	-	
		$V_{GE} = 15V$ , $I_C = 200A$ , $T_J = 175^{\circ}C$	-	2.1	-	
Total Gate Charge	Qg	$V_{CC} = 600V,$ $V_{GE} = 0/15V,$ $I_{C} = 200A$	-	0.96	-	μC
Internal Gate Resistance	R <sub>Gint</sub>	-	-	2.0	-	Ω
Input Capacitance	C <sub>iss</sub>	V <sub>CE</sub> = 25V,	-	19.3	-	
Output Capacitance	C <sub>oss</sub>	V <sub>GE</sub> = 0V,	-	0.82	-	nF
Reverse Transfer Capacitance	C <sub>rss</sub>	f = 1MHz	-	0.20	-	
Turn-on Delay time	t <sub>d(ON)</sub>	V <sub>CC</sub> = 600V,	-	150	-	- ns
Rise Time	t <sub>r</sub>		-	34	-	
Turn-off Delay time	t <sub>d(OFF)</sub>	$V_{GE} = \pm 15V,$ $R_G = 2\Omega,$	-	301	-	
Fall Time	t <sub>f</sub>	$I_C = 200A,$ $L_{load} = 0.82mH,$	-	172	-	
Turn-On Switching Loss	E <sub>on</sub>	Energy losses include "tail" and diode reverse	-	10.9	-	
Turn-Off Switching Loss	E <sub>off</sub>	recovery.	-	13.88	-	mJ
IGBT Total Switching Loss	E <sub>ts</sub>		-	24.78	-	
Turn-on Delay time	t <sub>d(ON)</sub>		-	157	-	
Rise Time	t <sub>r</sub>	$V_{CC} = 600V,$ $V_{GE} = \pm 15V,$	-	44	-	
Turn-off Delay time	t <sub>d(OFF)</sub>	$R_G = 2\Omega$ , $I_C = 200A$ ,	-	414	-	ns
Fall Time	t <sub>f</sub>	$L_{load} = 0.82 mH$ ,	-	298	-	
Turn-On Switching Loss	Eon	Energy losses include "tail" and diode reverse	1	18.7	1	
Turn-Off Switching Loss	E <sub>off</sub>	recovery. T <sub>J</sub> = 150°C	-	23.8	-	mJ
IGBT Total Switching Loss	E <sub>ts</sub>	., - 150 C	-	42.5	-	
Short Circuit Collector Current	I <sub>C(SC)</sub>	$V_{GE}$ = 15V, $V_{CC} \le 600V$ , $t_{SC} \le 10\mu s$	-	790	-	А



# Diode, Inverter

### **Absolute Maximum Ratings**

Parameter	Symbol	Limit	Unit
Repetitive Peak Reverse Voltage	$V_{RRM}$	1200	V
Continuous DC Forward Current	I <sub>F</sub>	200	
Repetitive Peak Forward Current (t <sub>P</sub> = 1ms)	I <sub>FRM</sub>	400	A

#### **Electrical Characteristics** (1)

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Diode Forward Voltage		I <sub>F</sub> = 200A	-	1.95	2.35		
	V <sub>F</sub>	I <sub>F</sub> = 200A T <sub>J</sub> = 150°C	-	1.75	=	v	
		I <sub>F</sub> = 200A T <sub>J</sub> = 175°C	-	1.7	ı		
Diode Reverse-Recovery Charge	$Q_{rr}$		-	14.6	-	μC	
Diode Peak Reverse-Recovery Current	I <sub>rrm</sub>	$V_R = 600V$ , $I_F = 200A$ , $dI_F/dt = -4200 A/\mu s$	-	180		Α	
Diode Reverse-Recovery Loss	E <sub>rr</sub>		-	5.56	-	mJ	

# **Module**

### **Absolute Maximum Ratings**

Parameter	Symbol	Limit	Unit
Maximum Junction Temperature	Tj	-40 to +175	
Operating Junction Temperature	T <sub>vj op</sub>	-40 to +150	°C
Storage Temperature	$T_{stg}$	-40 to +125	
Isolation Voltage ( f = 50 Hz, t = 1 min)	V <sub>ISO</sub>	4.0	kV

#### **Characteristics**

Parameter	Symbol	Min	Тур	Max	Unit
Material of Module Baseplate	-	-	Cu	1	-
Internal Isolation	-	-	Al <sub>2</sub> O <sub>3</sub>	-	
Creepage Distance, Terminal to Heatsink	-	-	29	-	mm
Creepage Distance, Terminal to Terminal	-	-	23	-	mm
Clearance, Terminal to Heatsink	-	-	23	-	mm



### JG1G200F120DG

Clearance, Terminal to Terminal	-	-	11	-	mm
Stray Inductance, Module	L <sub>SCE</sub>	-	20	-	nH
Module Lead Resistance, Terminal to Chip	R <sub>CC'+EE'</sub>	-	0.7	-	mΩ
Junction-to-Case Thermal Resistance, per IGBT, Inverter	R <sub>өлс</sub>	-	0.12	-	°C/W
Junction-to-Case Thermal Resistance, per Diode, Inverter		-	0.2	-	
Case-to-Heatsink Thermal Resistance, per IGBT, Inverter	R <sub>ech</sub>	-	0.034	-	
Case-to-Heatsink Thermal Resistance, per Diode, Inverter		-	0.05	-	°C/W
Case-to-Heatsink Thermal Resistance, per Module		-	0.01	-	
Mounting Torque for Module Mounting, Screw M6	М	3.0	-	6.0	Nm
Terminal Connection Torque, Screw M6	М	2.5	-	5.0	Nm
Weight per Module	G	-	320	-	g

(1)  $T_J = 25$ °C unless otherwise specified.

(2)  $t_r$ : from 10% of Ic to 90% of Ic;  $t_f$ : from 90% of Ic to 10% of Ic;

 $E_{on}\!\!:$  from 10% of  $V_{GE}$  to 10% of  $V_{CE};\quad E_{off}\!\!:$  from 90% of  $V_{GE}$  to 10% of Ic.



# • Typical Electrical Characteristics

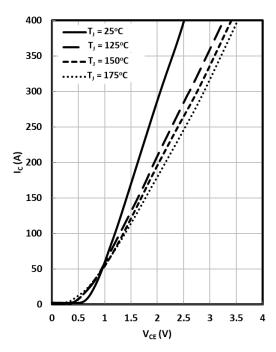


Fig. 1 IGBT (Inverter) Output Characteristics

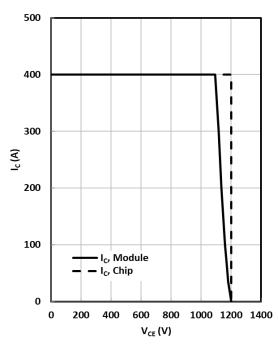


Fig. 3 RBSOA

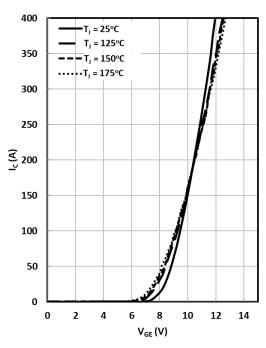


Fig. 2 IGBT (Inverter) Transfer Characteristics

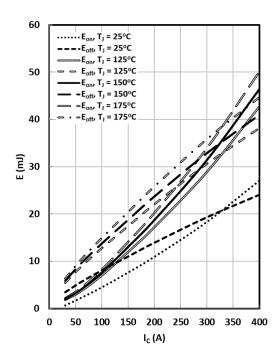


Fig. 4 IGBT Switching Loss vs. Ic  $(V_{CC} = 600V, V_{GE} = \pm 15V, R_G = 2\Omega)$ 



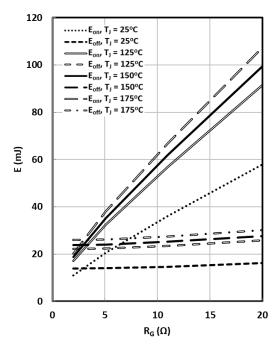
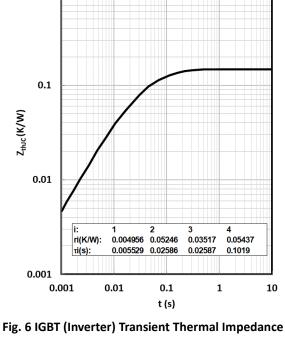


Fig. 5 IGBT Switching Loss vs. R<sub>G</sub>

 $(V_{CC} = 600V, V_{GE} = \pm 15V, I_C = 200A)$ 



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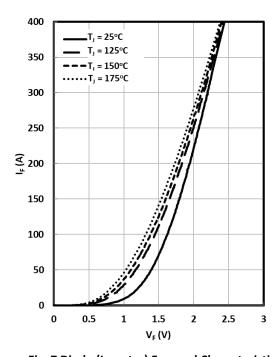


Fig. 7 Diode (Inverter) Forward Characteristics

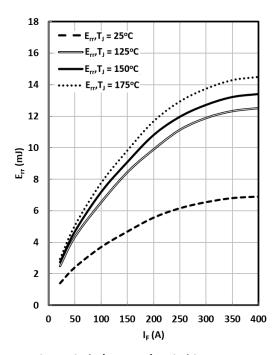


Fig. 8 Diode (Inverter) Switching Loss vs. IF

 $(V_{CC} = 600V, R_G = 2\Omega)$ 



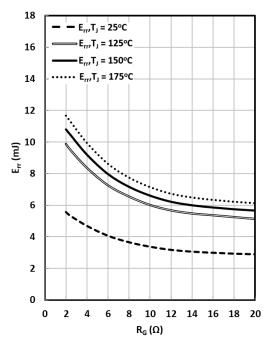


Fig. 9 Diode (Inverter) Switching Loss vs.  $R_G$  ( $V_{CC}$  = 600V,  $I_F$  = 200A)

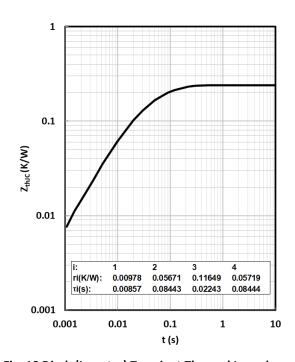
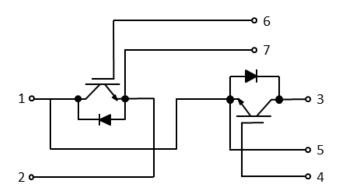


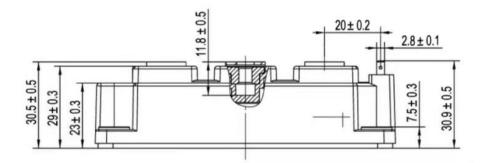
Fig. 10 Diode(Inverter) Transient Thermal Impedance

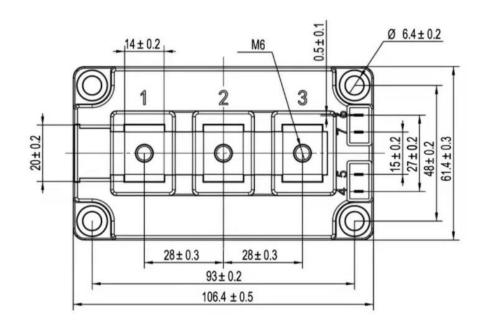


# • Circuit diagram



# • Package Dimensions





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